

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ASMMC.032DV1APPLICATION NO.  
10/781,574INFORMATION DISCLOSURE STATEMENT  
BY APPLICANTAPPLICANT  
Hujanen et al.FILING DATE  
February 17, 2004GROUP  
1773

(USE SEVERAL SHEETS IF NECESSARY)



## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>JS</i>	1.	5,780,175	7/14/98	Chen et al.			
	2.	5,939,334	8/17/99	Nguyen et al.			
	3.	5,998,048	12/7/99	Jin et al.			
	4.	6,006,763	12/28/99	Mori et al.			
	5.	6,143,658	11/7/00	Donnelly, Jr. et al.			
	6.	6,144,060	11/7/00	Park et al.			
	7.	6,404,191 B2	6/11/02	Daughton et al.			
	8.	6,478,931 B1	11/12/02	Wadley et al.			
	9.	6,617,173	09/09/03	Sneh			
	10.	6,551,399 B1	04/22/03	Sneh et al.			
	11.	4,058,430	11/15/77	Suntola et al.	156	611	11/25/75
	12.	5,711,811	01/27/98	Suntola et al.	118	711	11/28/95
	13.	5,916,365	06/29/99	Sherman	117	92	08/16/96
	14.	6,128,160	10/03/00	Yamamoto	360	113	04/24/98
	15.	6,153,062	11/28/00	Saito et al	204	192.2	12/10/98
<i>JS</i>	16.	6,342,277	01/29/02	Sherman	427	562	04/14/99

## FOREIGN PATENT DOCUMENTS

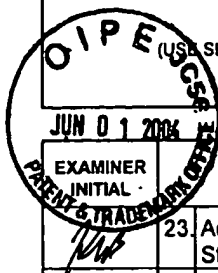
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>JS</i>	17.	JP 62221102	9/29/87	Japan			Abstract	
	18.	WO 02/09126 A2	7/18/01	PCT				
	19.	WO 02/09158 A2	7/18/01	PCT				
	20.	WO 00/38191	06/29/00	PCT				
	21.	WO 01/88972 A1	11/22/01	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>JS</i>	22. XP-002223616, "5 <sup>th</sup> Asian Symposium on Information Storage Technology (ASIST), Hong Kong, China, November 14-16, 2000.

EXAMINER	<i>John M. Ricks</i>	DATE CONSIDERED	<i>4/26/05</i>
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\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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		FILING DATE February 17, 2004	GROUP 1773



EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
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EXAMINER	<i>Kuni M. Kato</i>	DATE CONSIDERED	<i>4/21/05</i>
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